

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S18 2	2033	(si silicon) near5 (silicon near2 carbide or sic) same (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 17:50
S18 1	0	(si silicon) near5 "on" near10 (silicon near2 carbide or sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 17:50
S18 4	243	substrate near5 (si silicon) near5 (silicon near2 carbide or sic) near4 (layer or film) same (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 17:51
S18 3	1245	(si silicon) near5 (silicon near2 carbide or sic) near10 substrate same (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 17:51
S18 6	318	substrate near5 ((si silicon) and (silicon near2 carbide or sic)) near4 (layer or film) near10 (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 17:53
S18 5	193	substrate near5 (si silicon) near5 (silicon near2 carbide or sic) near4 (layer or film) near10 (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 17:53
S18 7	56	substrate near5 ((si) and (silicon near2 carbide or sic)) near4 (layer or film) near10 (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 17:57
S18 8	153	substrate near5 (silicon or si) same (sic or silicon near2 carbide) near5 buffer same (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 17:58
S19 0	0	(sapphire or ("al.sub.2o.sub.3"))) near10 nitridiz\$7 near10 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 18:02

S18 9	82	substrate near5 (silicon or si) near10 (sic or silicon near2 carbide) near5 buffer same (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 18:02
S19 1	5	(sapphire or ("al.sub.2o.sub.3")) near10 nitridiz\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 18:03
S19 2	502	(sapphire or ("al.sub.2o.sub.3")) near10 nitrid\$5 near10 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 18:05
S19 3	7	(sapphire or ("al.sub.2o.sub.3")) near10 nitrid\$5 near10 buffer near10 (ammonia or "nh.sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 18:09
S19 4	9	(sapphire or ("al.sub.2o.sub.3")) near10 nitriding near10 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 11:30
S19 5	48	(sapphire or ("al.sub.2o.sub.3")) near10 nitriding	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 11:38
S19 6	51	(sapphire or ("al.sub.2o.sub.3")) near10 nitrid\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:05
S19 8	78	(zno or zinc near2 oxide) near20 sputter\$6 near10 (sapphire or "al. sub.2o.sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:22
S19 7	69	(sic or silicon adj carbide) near10 buffer near10 (si near3 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:22
S19 9	9	buffer near10 (zno or zinc near2 oxide) near20 sputter\$6 near10 (sapphire or "al.sub.2o.sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:24

S20 1	1	(zno or zinc near2 oxide) near20 sputter:\$6 near10 (sapphire or "al. sub.2o.sub.3") same nitride near4 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:35
S20 0	8	(zno cr zinc near2 oxide) near20 sputter:\$6 near10 (sapphire or "al. sub.2o.sub.3") same (gallium near2 nitride or gan)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:36
S20 2	10	(zno or zinc near2 oxide) near20 sputter:\$6 near10 (sapphire or "al. sub.2o.sub.3") same buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:37
S20 4	58	buffer near10 (zno or zinc near2 oxide) near10 (sapphire or "al.sub.2o.sub.3") same (gan or gallium adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:38
S20 3	84	buffer near10 (zno or zinc near2 oxide) near10 (sapphire or "al.sub.2o.sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:38
S20 6	2	"5770887".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:46
S20 5	42	buffer near10 (zno or zinc near2 oxide) near10 (sapphire or "al.sub.2o.sub.3") same (gan or gallium adj nitride) near10 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:46
L1	1	(zno or zinc near2 oxide) near10 RF near10 (sapphire or "al.sub.2o. sub.3") near10 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 14:59
L2	18	(zno or zinc near2 oxide) near10 RF near10 (sapphire or "al.sub.2o. sub.3")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 16:21
L5	25	lattice near2 constant near5 (aln) near5 (angstrom or ang)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 16:22

L4	133	lattice near2 constant near5 (aln)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 16:22
L3	85	lattice near2 constant near5 (gan and aln)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 16:22
L6	25	lattice near2 constant near5 (aln) near5 (angstrom or ang or ".ang")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 16:23
L8	2	"20030012984".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 16:25
L10	104	lattice near2 constant near5 silicon near5 (angstrom or ang or ".ang")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 16:28
L9	177808	lattice near2 constant near5 siliconnear5 (angstrom or ang or .ang")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 16:28
L7	25	lattice near2 constant near5 sapphire near5 (angstrom or ang or ".ang")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 16:28